NUD3160

Industrial Inductive Load Driver

This MicroIntegration™ part provides a single component solution to switch inductive loads such as relays, solenoids, and small DC motors without the need of a free−wheeling diode. It accepts logic level inputs, thus allowing it to be driven by a large variety of devices including logic gates, inverters, and microcontrollers.

Features

- Provides Robust Interface between D.C. Relay Coils and Sensitive Logic
- Capable of Driving Relay Coils Rated up to 150 mA at 12 V, 24 V or 48 V
- Replaces 3 or 4 Discrete Components for Lower Cost
- Internal Zener Eliminates Need for Free−Wheeling Diode
- Meets Load Dump and other Automotive Specs

Typical Applications

- Automotive and Industrial Environment
- Drives Window, Latch, Door, and Antenna Relays

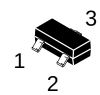
Benefits

- Reduced PCB Space
- Standardized Driver for Wide Range of Relays
- Simplifies Circuit Design and PCB Layout
- Compliance with Automotive Specifications

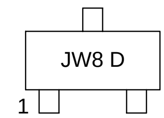
ON Semiconductor®

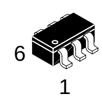
http://onsemi.com

MARKING DIAGRAMS

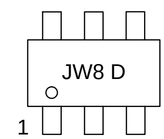


SOT−23
CASE 318
STYLE 21





SC−74
CASE 318F
STYLE 7

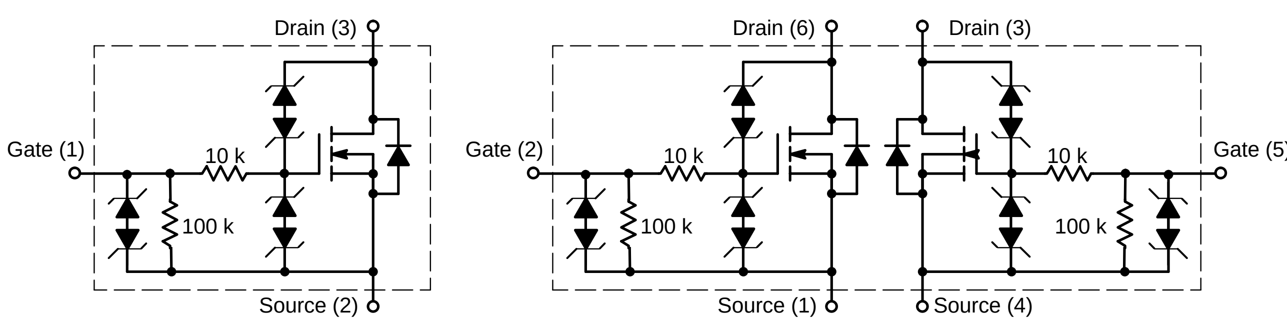


JW8 = Specific Device Code
D = Date Code

ORDERING INFORMATION

Device	Package	Shipping†
NUD3160LT1	SOT−23	3000 Tape & Reel
NUD3160DMT1	SC−74	3000 Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



CASE 318　　CASE 318F

Figure 1. Internal Circuit Diagrams

MAXIMUM RATINGS (T_J = 25°C unless otherwise specified)

Symbol	Rating	Value	Unit
V_{DSS}	Drain−to−Source Voltage – Continuous (T_J = 125°C)	60	V
V_{GSS}	Gate−to−Source Voltage – Continuous (T_J = 125°C)	12	V
I_D	Drain Current – Continuous (T_J = 125°C)	150	mA
E_Z	Single Pulse Drain−to−Source Avalanche Energy (For Relay's Coils/Inductive Loads of 80 Ω or Higher) (T_J Initial = 85°C)	200	mJ
P_{PK}	Peak Power Dissipation, Drain−to−Source (Notes 1 and 2) (T_J Initial = 85°C)	20	W
E_{LD1}	Load Dump Pulse, Drain−to−Source (Note 3) R_{SOURCE} = 0.5 Ω, T = 300 ms) (For Relay's Coils/Inductive Loads of 80 Ω or Higher) (T_J Initial = 85°C)	60	V
E_{LD2}	Inductive Switching Transient 1, Drain−to−Source (Waveform: R_{SOURCE} = 10 Ω, T = 2.0 ms) (For Relay's Coils/Inductive Loads of 80 Ω or Higher) (T_J Initial = 85°C)	100	V
E_{LD3}	Inductive Switching Transient 2, Drain−to−Source (Waveform: R_{SOURCE} = 4.0 Ω, T = 50 μs) (For Relay's Coils/Inductive Loads of 80 Ω or Higher) (T_J Initial = 85°C)	300	V
Rev−Bat	Reverse Battery, 10 Minutes (Drain−to−Source) (For Relay's Coils/Inductive Loads of 80 Ω or more)	−14	V
Dual−Volt	Dual Voltage Jump Start, 10 Minutes (Drain−to−Source)	28	V
ESD	Human Body Model (HBM) According to EIA/JESD22/A114 Specification	2000	V

THERMAL CHARACTERISTICS

Symbol	Rating		Value	Unit
T_A	Operating Ambient Temperature		−40 to 125	°C
T_J	Maximum Junction Temperature		150	°C
T_{STG}	Storage Temperature Range		−65 to 150	°C
P_D	Total Power Dissipation (Note 4) Derating above 25°C	SOT−23	225 1.8	mW mW/°C
P_D	Total Power Dissipation (Note 4) Derating above 25°C	SC−74	380 3.0	mW mW/°C
$R_{\theta JA}$	Thermal Resistance Junction–to–Ambient (Note 4)	SOT−23 SC−74	556 329	°C/W

1. Nonrepetitive current square pulse 1.0 ms duration.
2. For different square pulse durations, see Figure 12.
3. Nonrepetitive load dump pulse per Figure 3.
4. Mounted onto minimum pad board.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Drain to Source Sustaining Voltage (I_D = 10 mA)	V_{BRDSS}	61	66	70	V
Drain to Source Leakage Current	I_{DSS}				μA
(V_{DS} = 12 V, V_{GS} = 0 V)		–	–	0.5	
(V_{DS} = 12 V, V_{GS} = 0 V, T_J = 125°C)		–	–	1.0	
(V_{DS} = 60 V, V_{GS} = 0 V)		–	–	50	
(V_{DS} = 60 V, V_{GS} = 0 V, T_J = 125°C)		–	–	80	
Gate Body Leakage Current	I_{GSS}				μA
(V_{GS} = 3.0 V, V_{DS} = 0 V)		–	–	60	
(V_{GS} = 3.0 V, V_{DS} = 0 V, T_J = 125°C)		–	–	80	
(V_{GS} = 5.0 V, V_{DS} = 0 V)		–	–	90	
(V_{GS} = 5.0 V, V_{DS} = 0 V, T_J = 125°C)		–	–	110	
ON CHARACTERISTICS					
Gate Threshold Voltage	$V_{GS(th)}$				V
(V_{GS} = V_{DS}, I_D = 1.0 mA)		1.3	1.8	2.0	
(V_{GS} = V_{DS}, I_D = 1.0 mA, T_J = 125°C)		1.3	–	2.0	
Drain to Source On−Resistance	$R_{DS(on)}$				Ω
(I_D = 150 mA, V_{GS} = 3.0 V)		–	–	2.4	
(I_D = 150 mA, V_{GS} = 3.0 V, T_J = 125°C)		–	–	3.7	
(I_D = 150 mA, V_{GS} = 5.0 V)		–	–	1.8	
(I_D = 150 mA, V_{GS} = 5.0 V, T_J = 125°C)		–	–	2.9	
Output Continuous Current	$I_{DS(on)}$				mA
(V_{DS} = 0.3 V, V_{GS} = 5.0 V)		150	200	–	
(V_{DS} = 0.3 V, V_{GS} = 5.0 V, T_J = 125°C)		100	–	–	
Forward Transconductance (V_{DS} = 12 V, I_D = 150 mA)	g_{FS}	–	400	–	mmho
DYNAMIC CHARACTERISTICS					
Input Capacitance (V_{DS} = 12 V, V_{GS} = 0 V, f = 10 kHz)	C_{iss}	–	30	–	pf
Output Capacitance (V_{DS} = 12 V, V_{GS} = 0 V, f = 10 kHz)	C_{oss}	–	14	–	pf
Transfer Capacitance (V_{DS} = 12 V, V_{GS} = 0 V, f = 10 kHz)	C_{rss}	–	6.0	–	pf
SWITCHING CHARACTERISTICS					
Propagation Delay Times:					ns
High to Low Propagation Delay; Figure 2, (V_{DS} = 12 V, V_{GS} = 3.0 V)	t_{PHL}	–	918	–	
Low to High Propagation Delay; Figure 2, (V_{DS} = 12 V, V_{GS} = 3.0 V)	t_{PLH}	–	798	–	
High to Low Propagation Delay; Figure 2, (V_{DS} = 12 V, V_{GS} = 5.0 V)	t_{PHL}	–	331	–	
Low to High Propagation Delay; Figure 2, (V_{DS} = 12 V, V_{GS} = 5.0 V)	t_{PLH}	–	1160	–	
Transition Times:					ns
Fall Time; Figure 2, (V_{DS} = 12 V, V_{GS} = 3.0 V)	t_f	–	2290	–	
Rise Time; Figure 2, (V_{DS} = 12 V, V_{GS} = 3.0 V)	t_r	–	618	–	
Fall Time; Figure 2, (V_{DS} = 12 V, V_{GS} = 5.0 V)	t_f	–	622	–	
Rise Time; Figure 2, (V_{DS} = 12 V, V_{GS} = 5.0 V)	t_r	–	600	–	

TYPICAL WAVEFORMS

(T_J = 25°C unless otherwise specified)

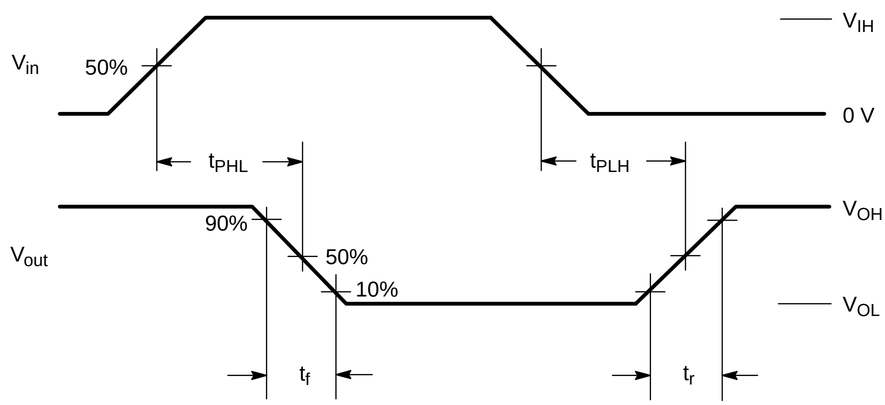


Figure 2. Switching Waveforms

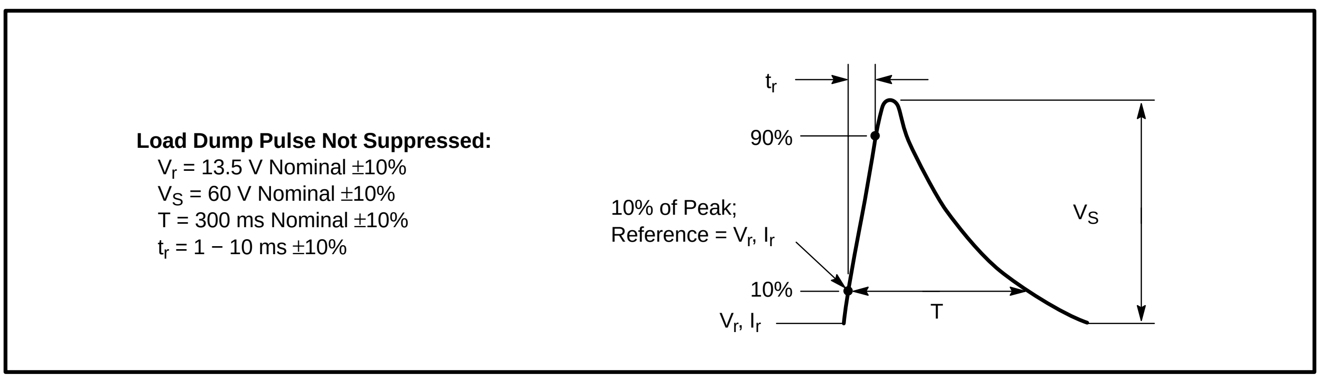


Figure 3. Load Dump Waveform Definition

TYPICAL PERFORMANCE CURVES

(T_J = 25°C unless otherwise specified)

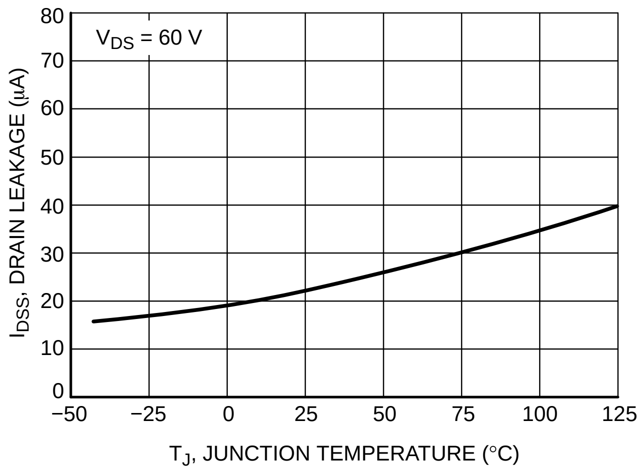


Figure 4. Drain−to−Source Leakage vs. Junction Temperature

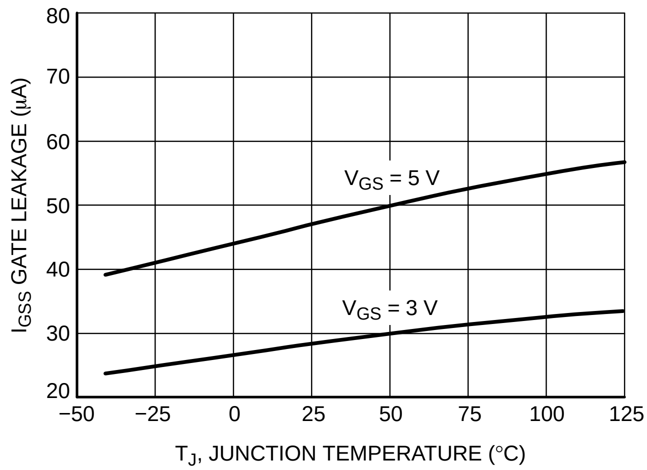


Figure 5. Gate−to−Source Leakage vs. Junction Temperature

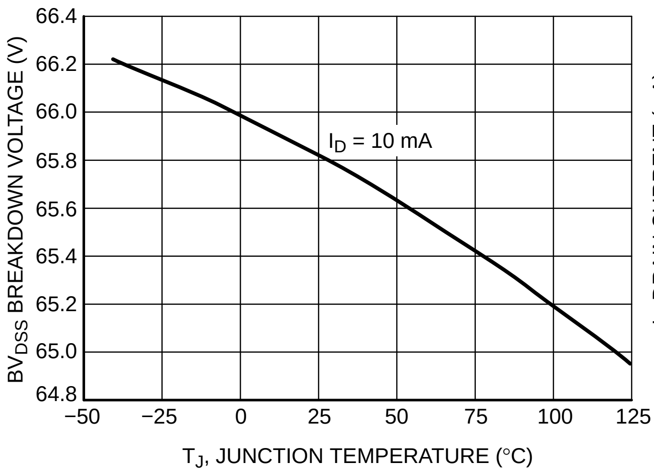


Figure 6. Breakdown Voltage vs. Junction Temperature

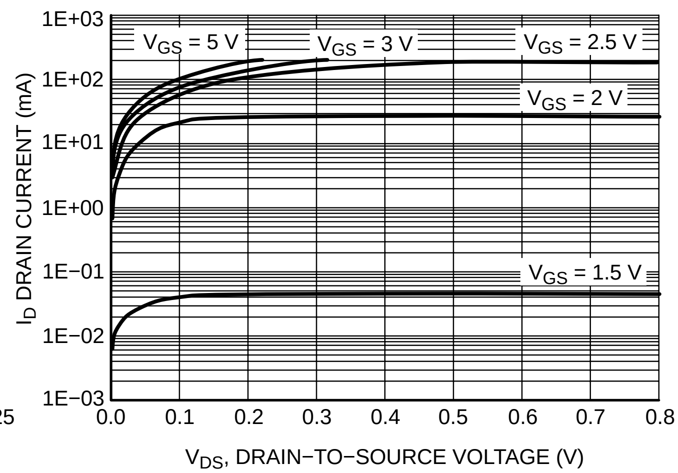


Figure 7. Output Characteristics

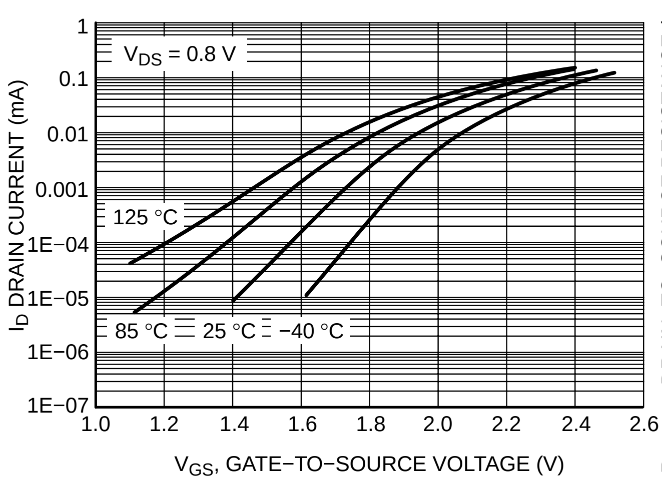


Figure 8. Transfer Function

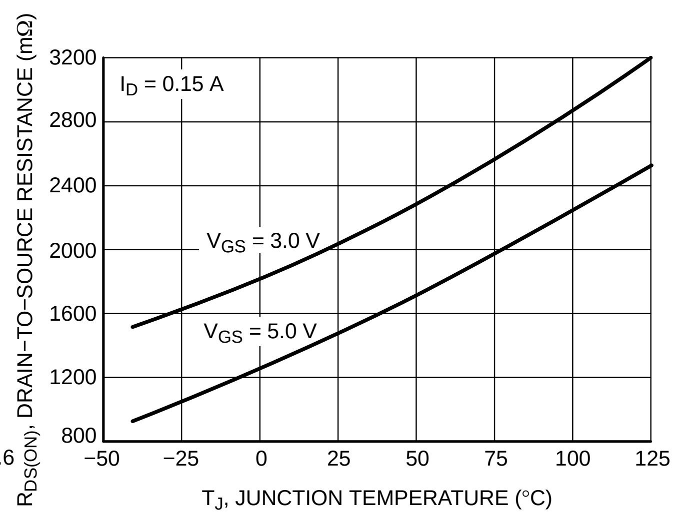


Figure 9. On Resistance Variation vs Junction Temperature

TYPICAL PERFORMANCE CURVES

(T_J = 25°C unless otherwise specified)

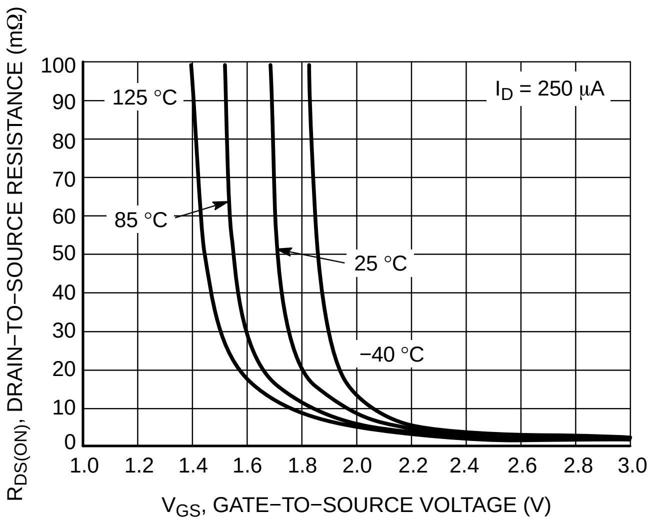


Figure 10. On Resistance Variation vs. Gate−to−Source Voltage

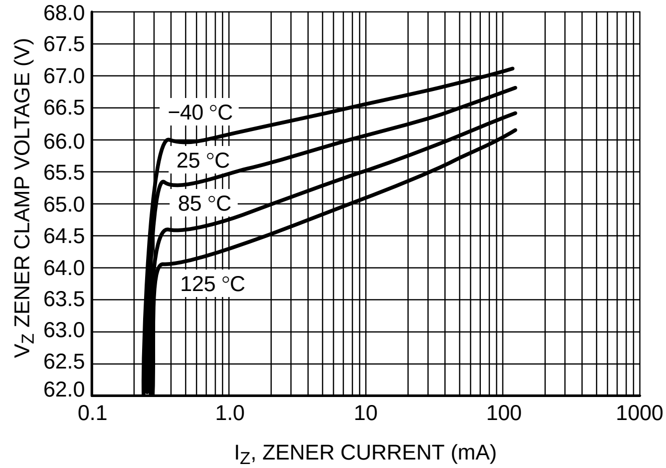


Figure 11. Zener Clamp Voltage vs. Zener Current

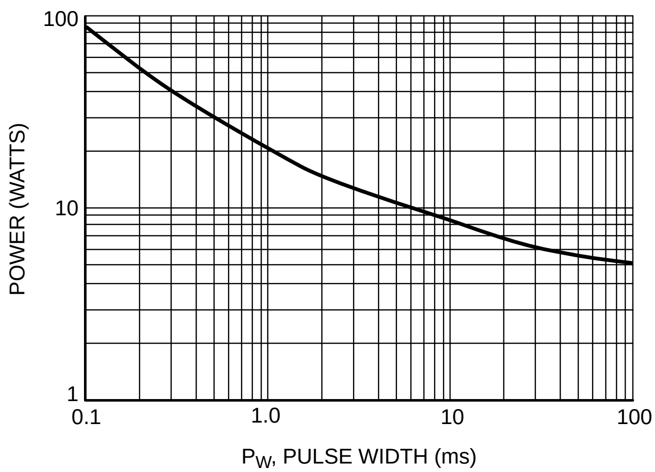


Figure 12. Maximum Non−repetitive Surge Power vs. Pulse Width

APPLICATIONS INFORMATION

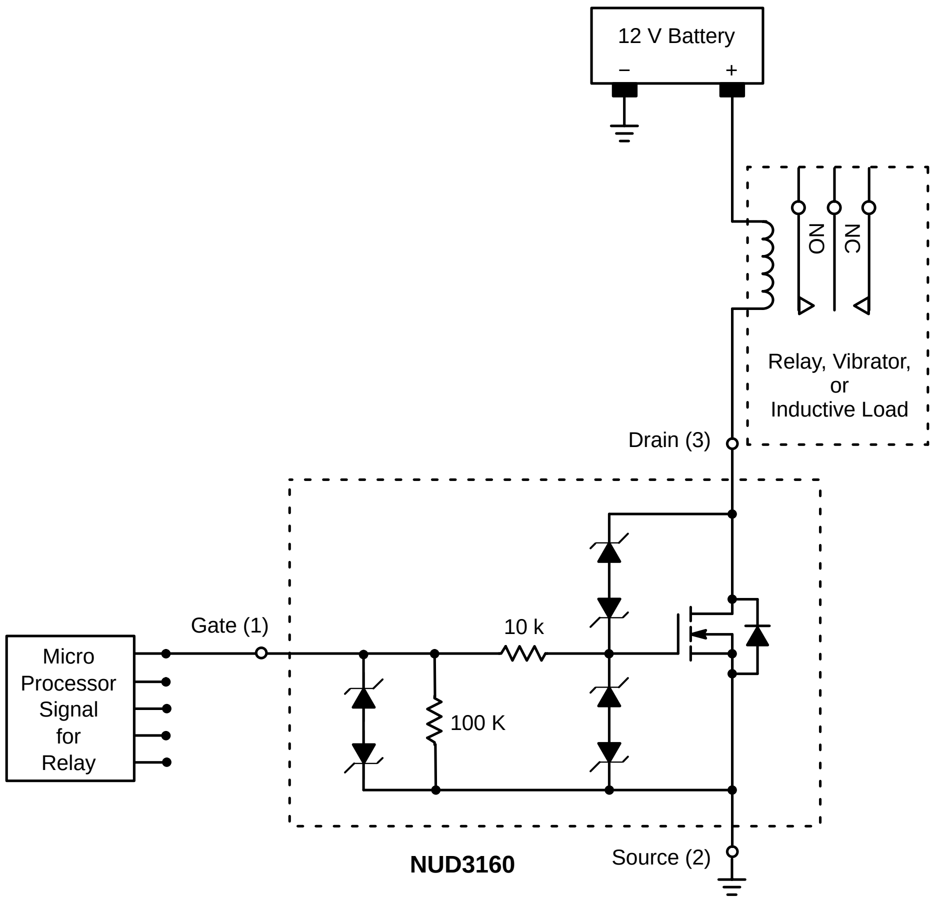
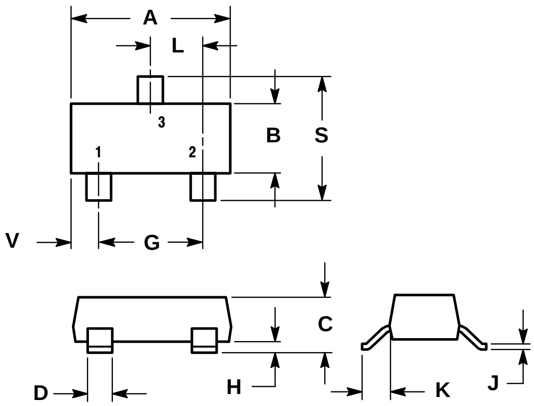


Figure 13. Applications Diagram

PACKAGE DIMENSIONS

SOT−23 (TO−236)
CASE 318−09
ISSUE AH

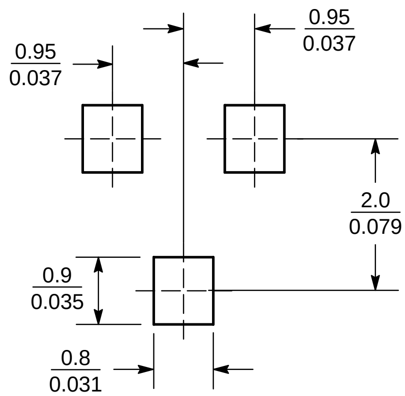


NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIUMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318−01, −02, AND −06 OBSOLETE, NEW STANDARD 318−09.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0385	0.0498	0.99	1.26
D	0.0140	0.0200	0.36	0.50
G	0.0670	0.0826	1.70	2.10
H	0.0040	0.0098	0.10	0.25
J	0.0034	0.0070	0.085	0.177
K	0.0180	0.0236	0.45	0.60
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.0984	2.10	2.50
V	0.0177	0.0236	0.45	0.60

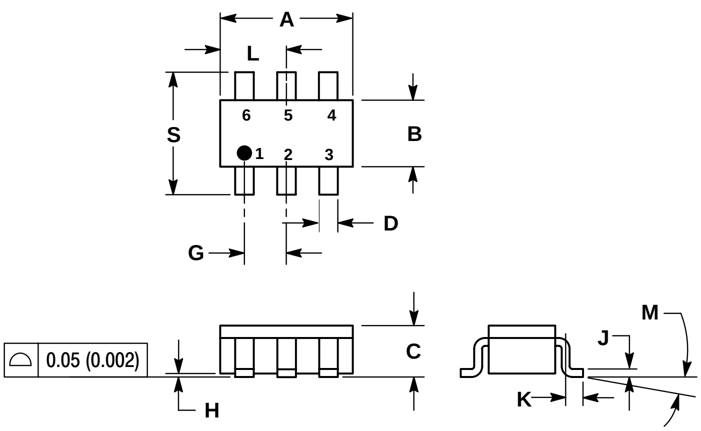
STYLE 21:
PIN 1. GATE
2. SOURCE
3. DRAIN

SOLDERING FOOTPRINT



PACKAGE DIMENSIONS

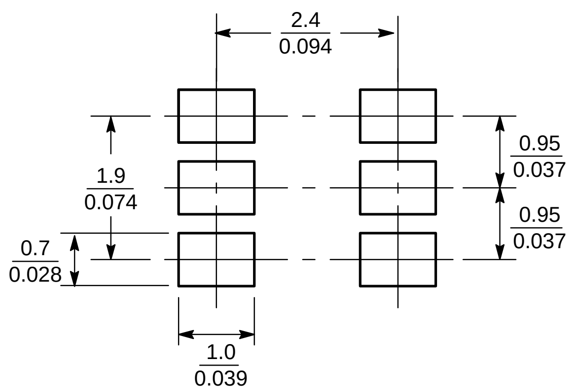
SC−74
CASE 318F−05
ISSUE K



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318F−01, −02, −03 OBSOLETE. NEW STANDARD 318F−04.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.1142	0.1220	2.90	3.10
B	0.0512	0.0669	1.30	1.70
C	0.0354	0.0433	0.90	1.10
D	0.0098	0.0197	0.25	0.50
G	0.0335	0.0413	0.85	1.05
H	0.0005	0.0040	0.013	0.100
J	0.0040	0.0102	0.10	0.26
K	0.0079	0.0236	0.20	0.60
L	0.0493	0.0649	1.25	1.65
M	0 °	10 °	0 °	10 °
S	0.0985	0.1181	2.50	3.00

SOLDERING FOOTPRINT



PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 61312, Phoenix, Arizona 85082−1312 USA
Phone: 480−829−7710 or 800−344−3860 Toll Free USA/Canada
Fax: 480−829−7709 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada

Japan: ON Semiconductor, Japan Customer Focus Center
2−9−1 Kamimeguro, Meguro−ku, Tokyo, Japan 153−0051
Phone: 81−3−5773−3850

ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.